

Fig.1A

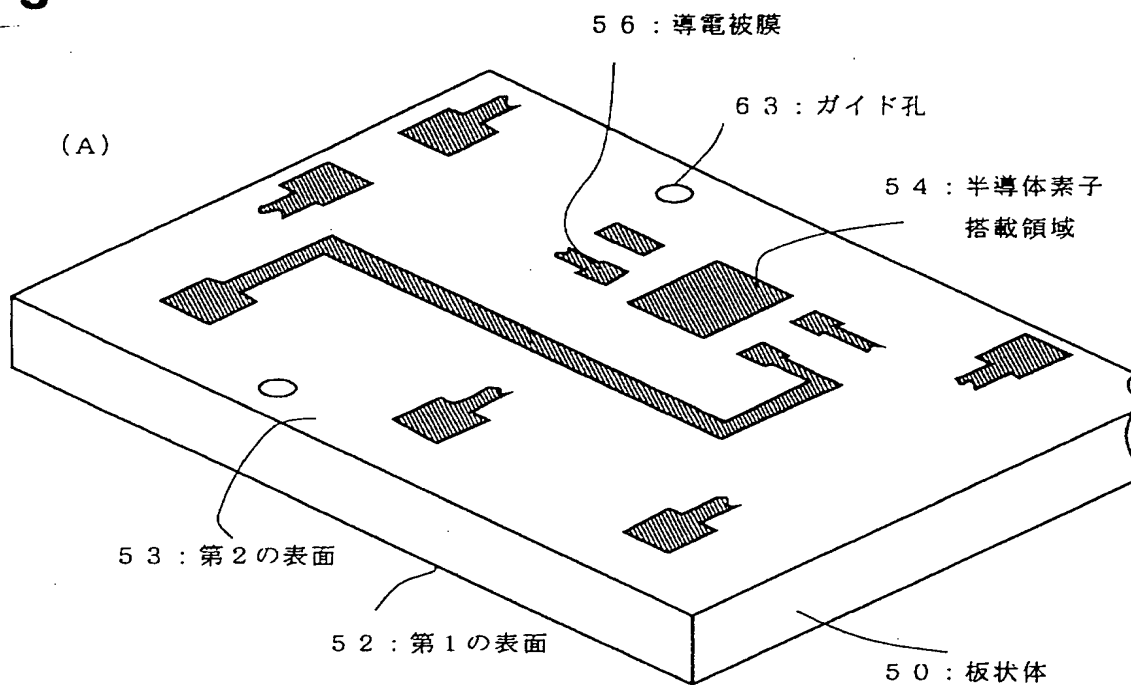


Fig.1B

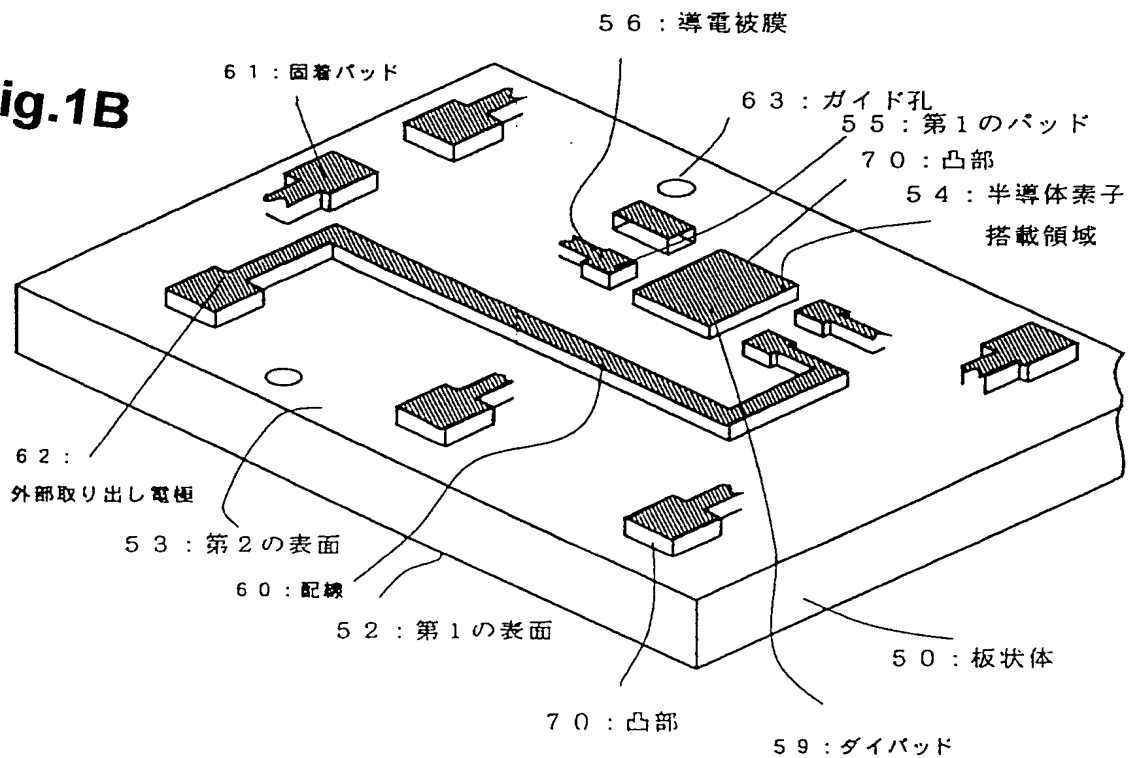
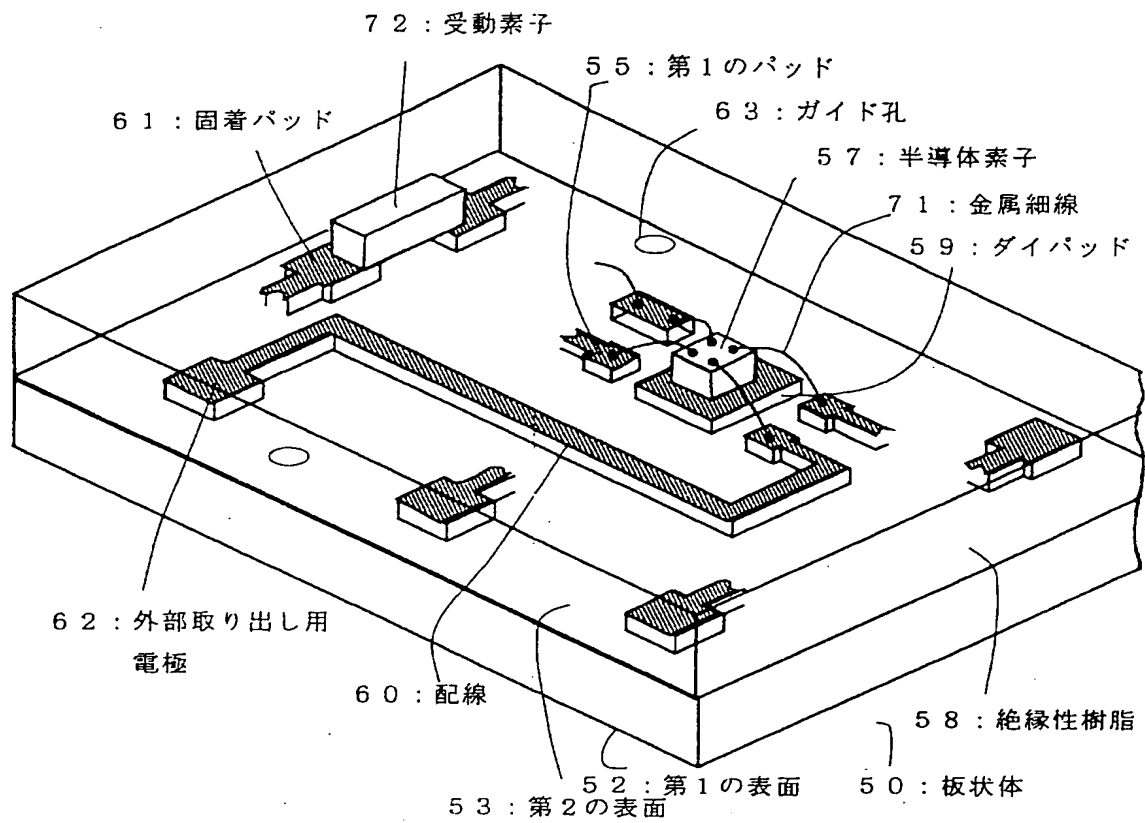


Fig.2



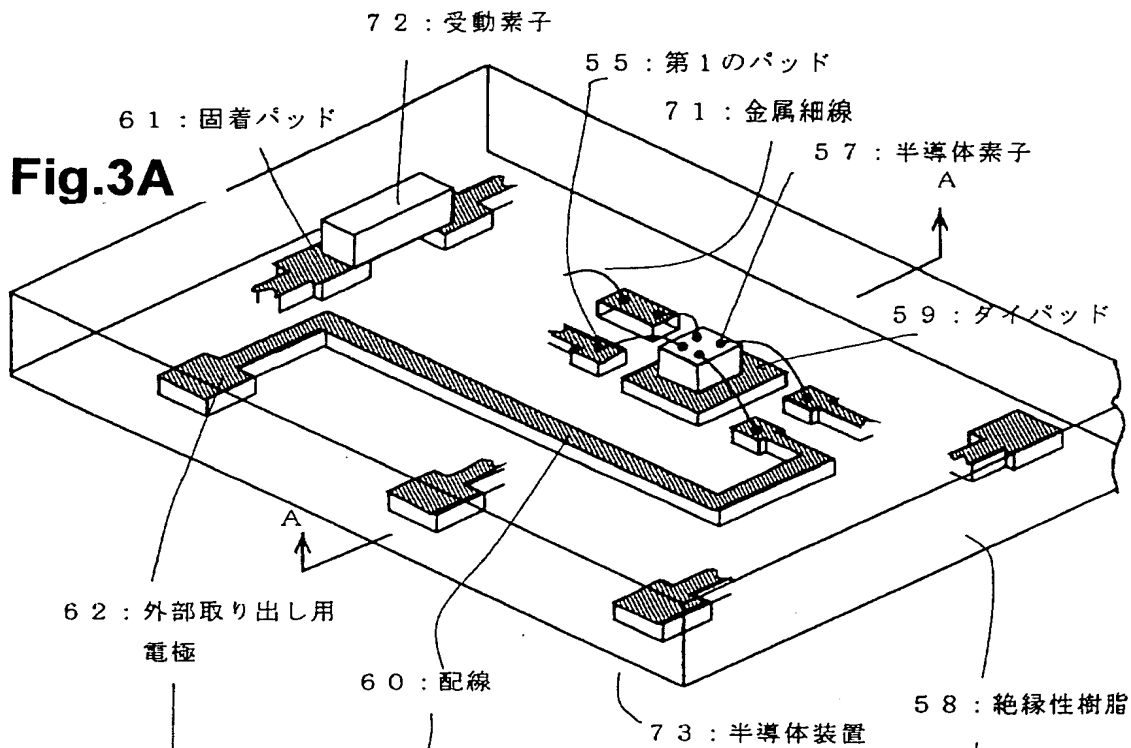


Fig.3B

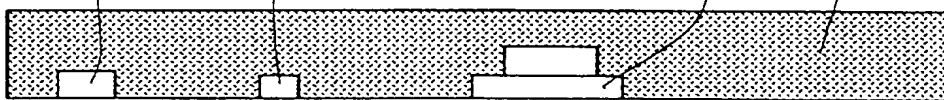


Fig.4

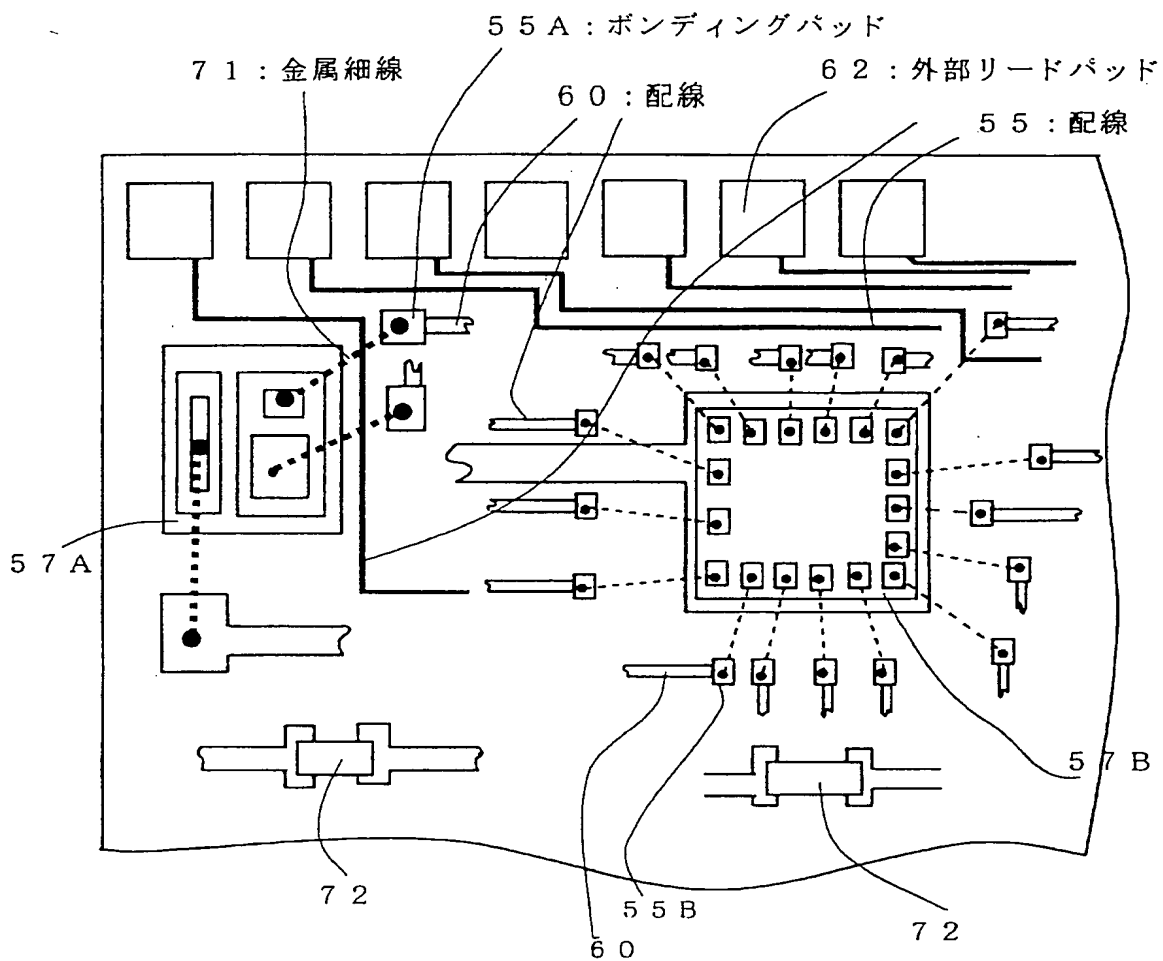


Fig.5A

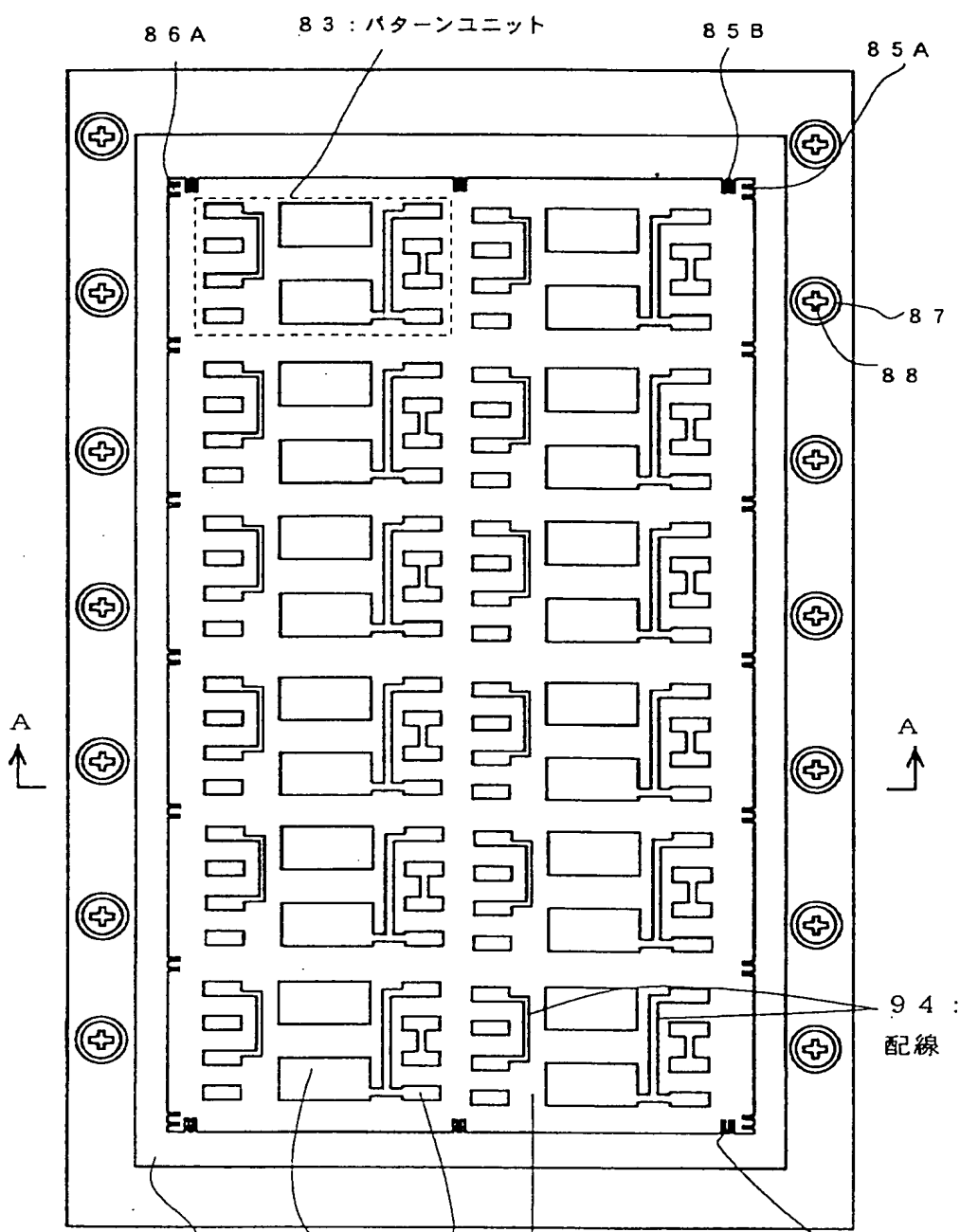
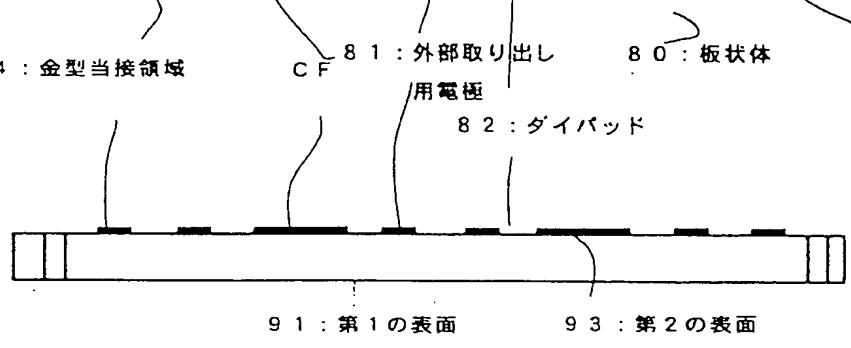


Fig.5B



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Fig.6A

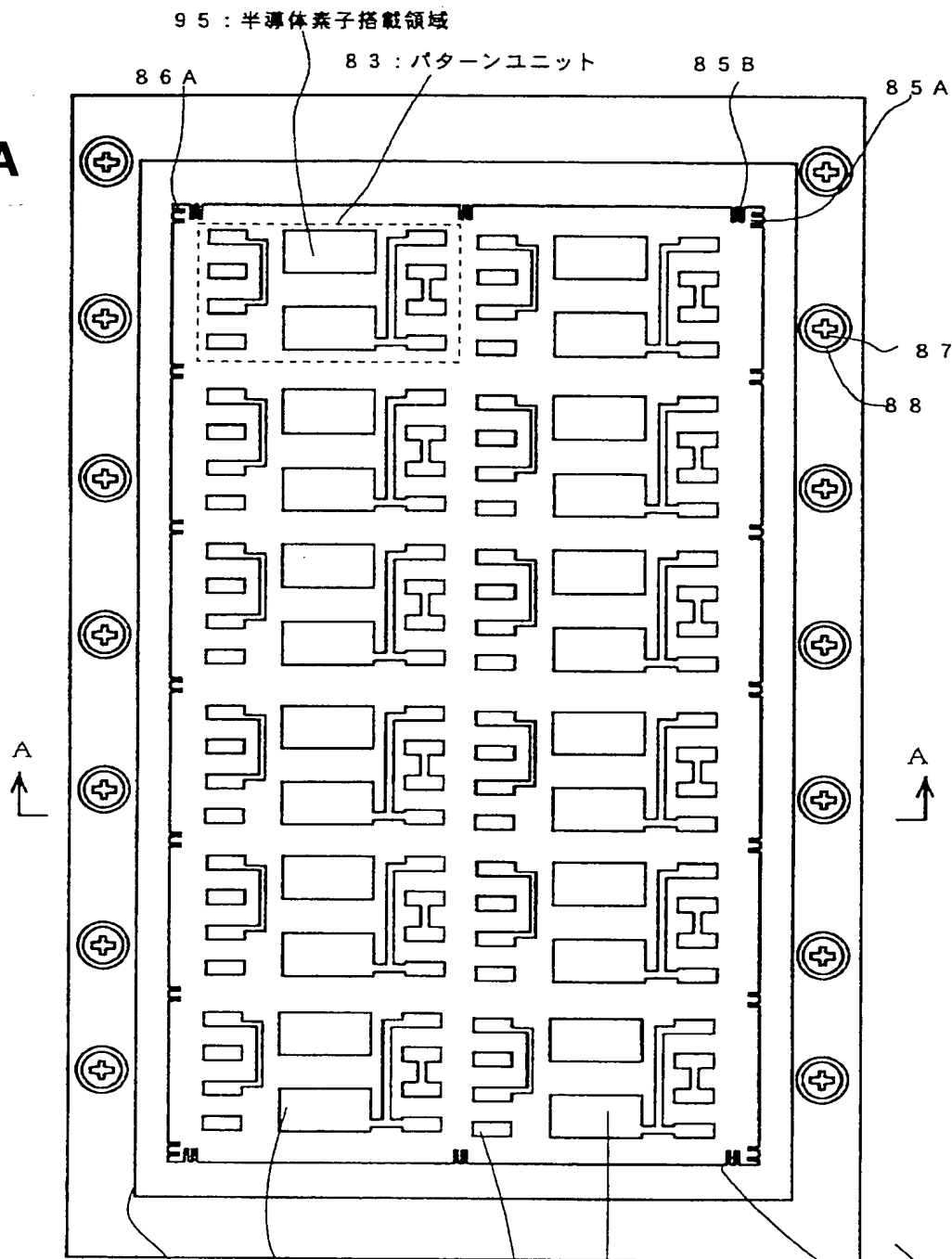
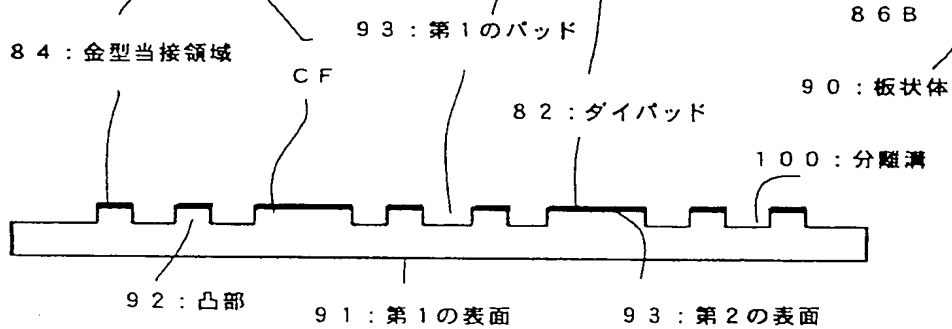


Fig.6B



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Fig.7A

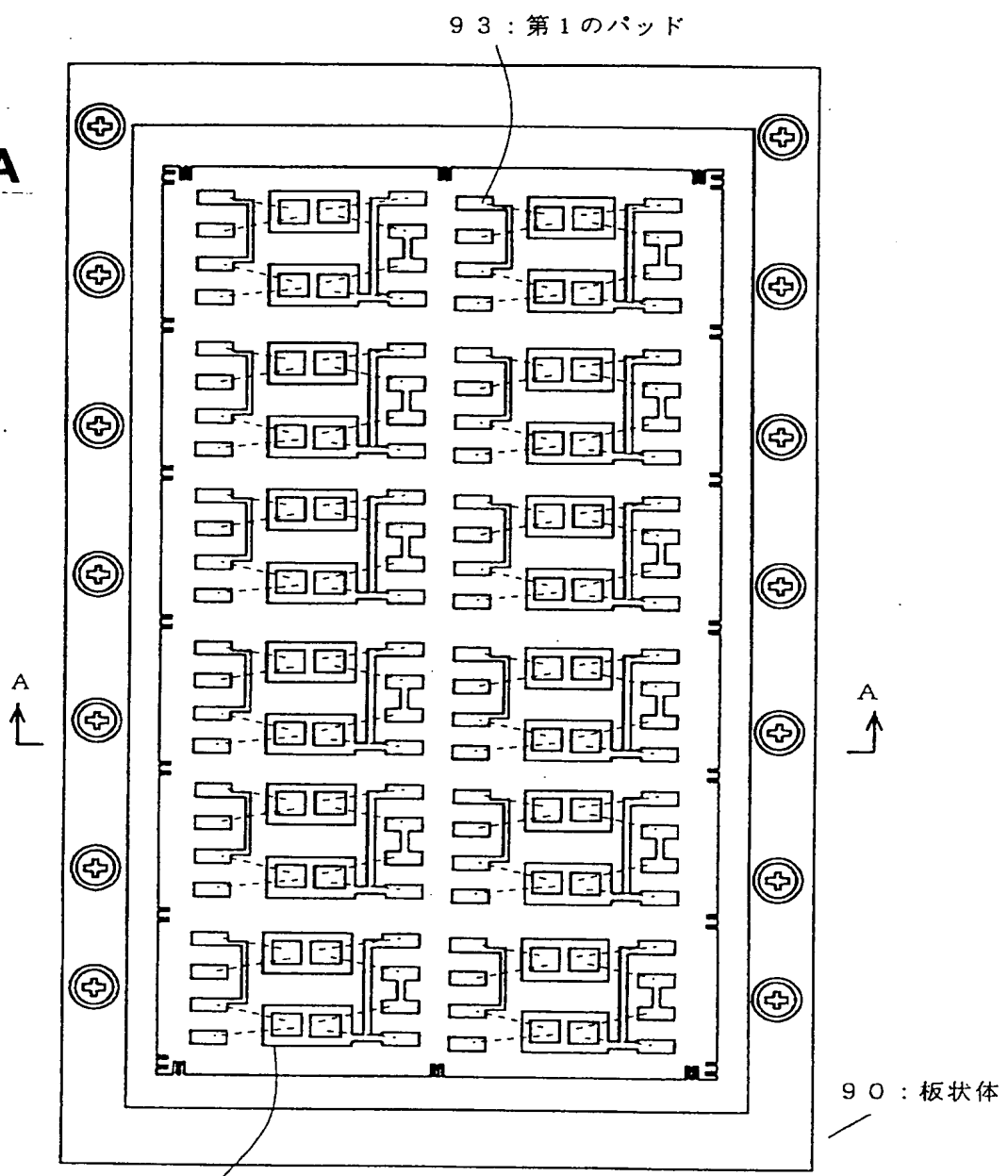
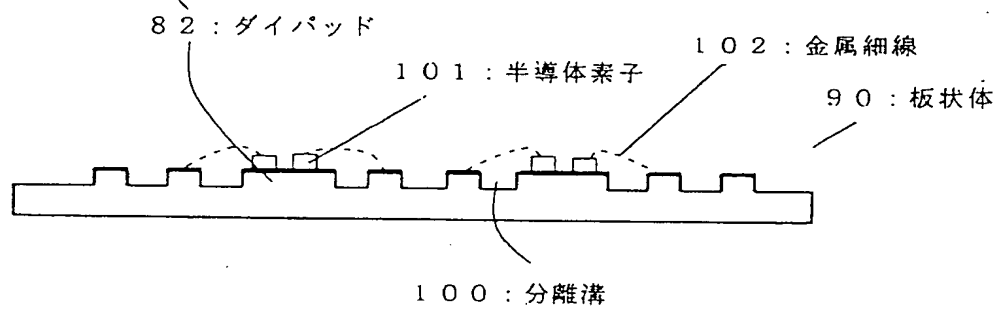
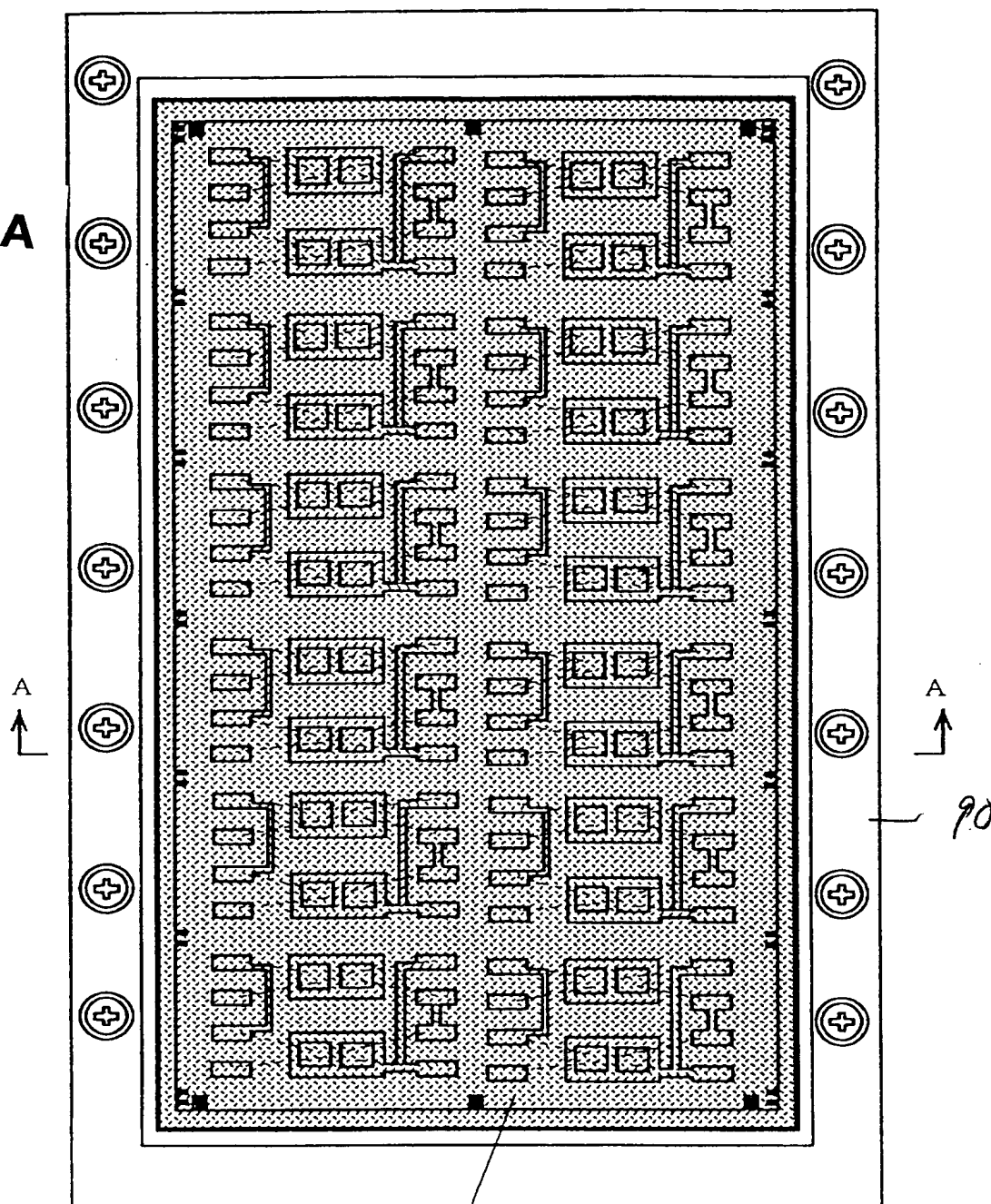


Fig.7B



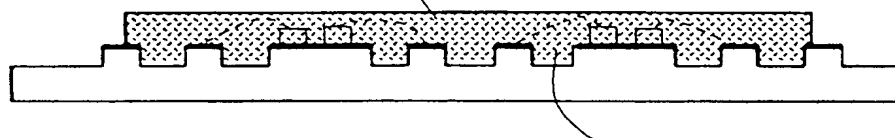
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Fig.8A



103 : 絶縁性樹脂

Fig.8B



100 : 分離溝

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Fig.9A

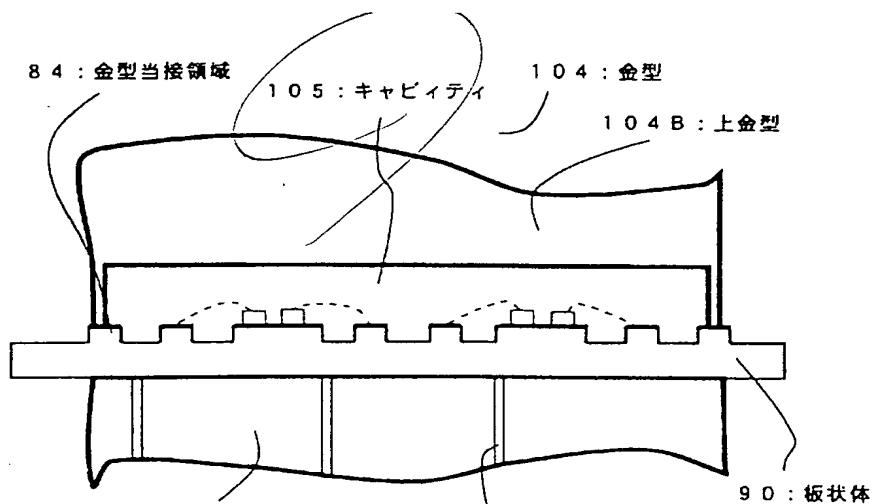


Fig.9B B) 105

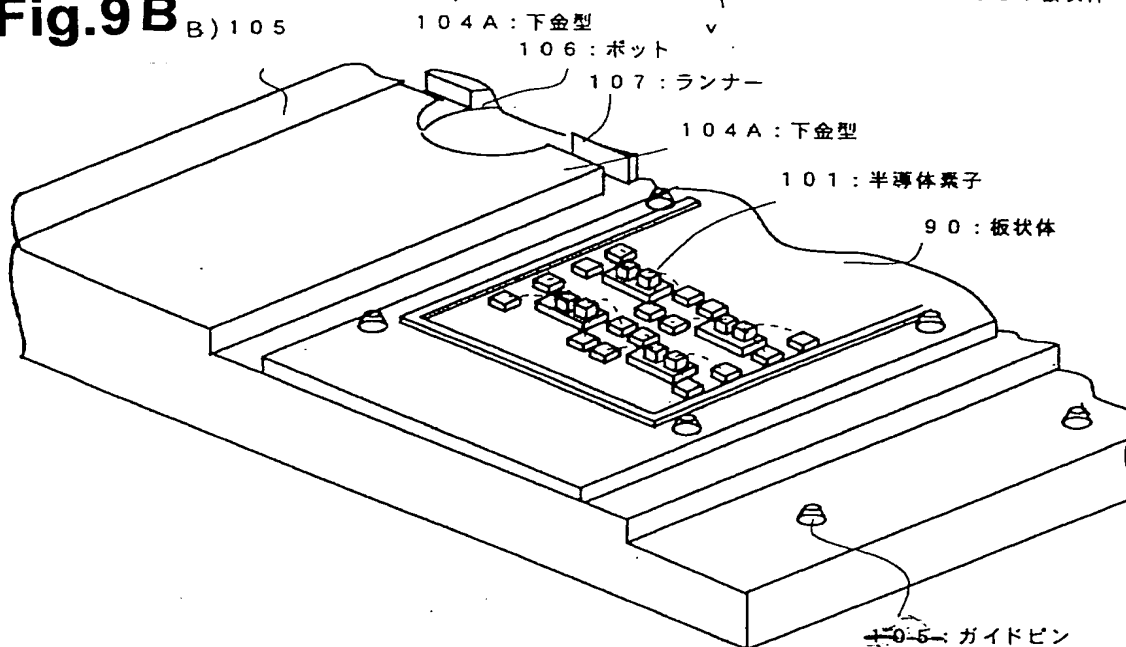
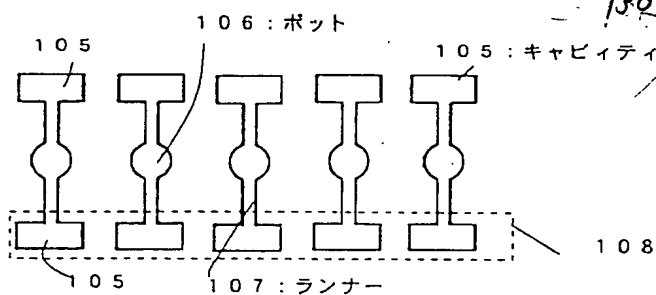


Fig.9C C)



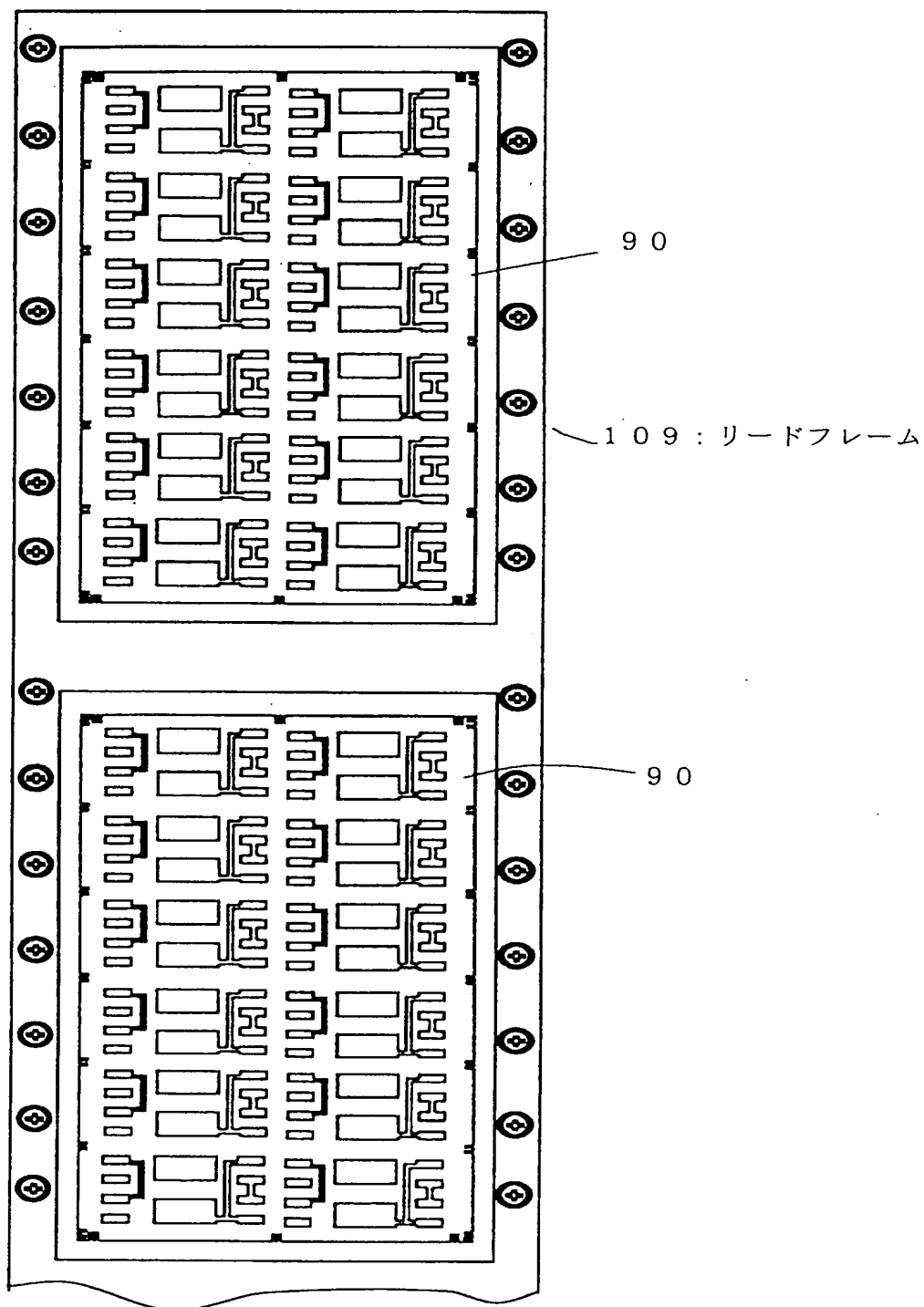
1-72

82: アイランド 81: 第1のパッド 100: 分離溝 103: 絶縁性樹脂

Figure 1 is a cross-sectional view of a semiconductor device. The device consists of a substrate with a thin layer 111 (凸部) on top. A layer 112 (絶縁被膜) is on the side walls. A layer 113 (半導体装置) is on top of the substrate. The device is shown in a cross-section with dashed lines indicating it is a repeating unit.

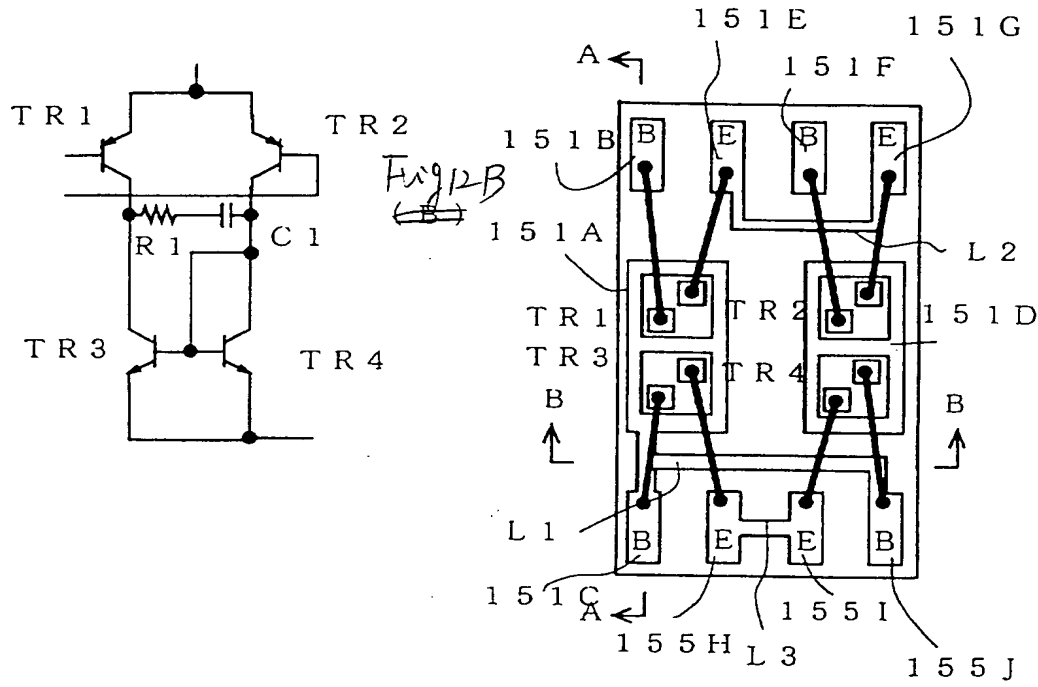
Fig.11

000001-21782560



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Fig.12 A



00679442-10000

Fig.12C

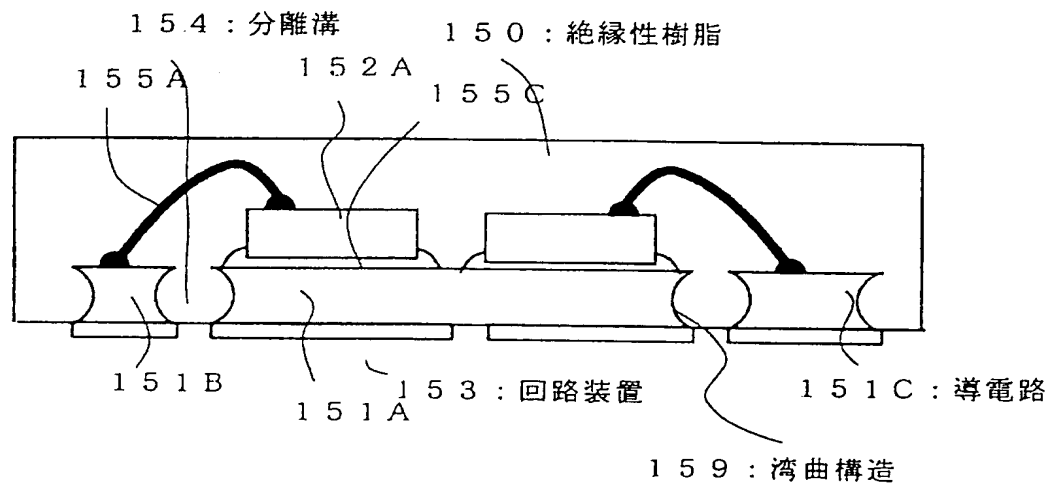


Fig.12D

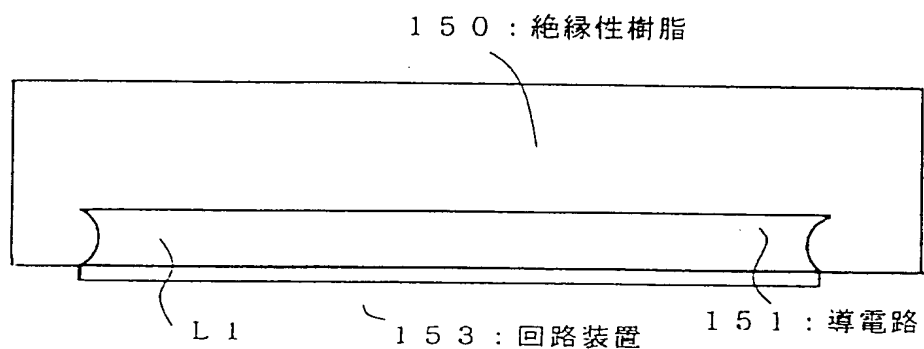
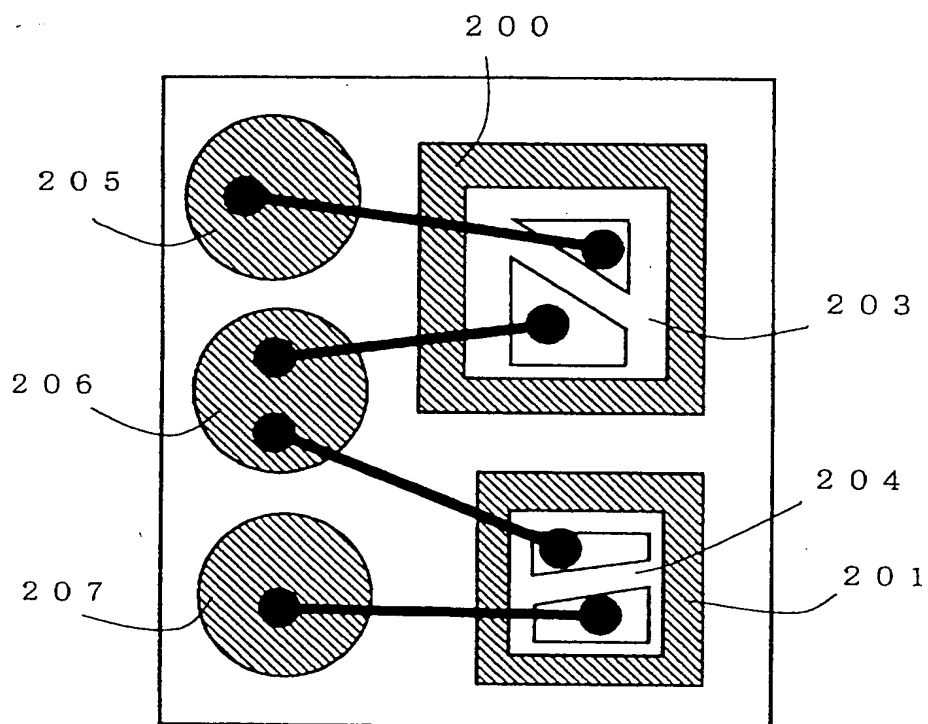
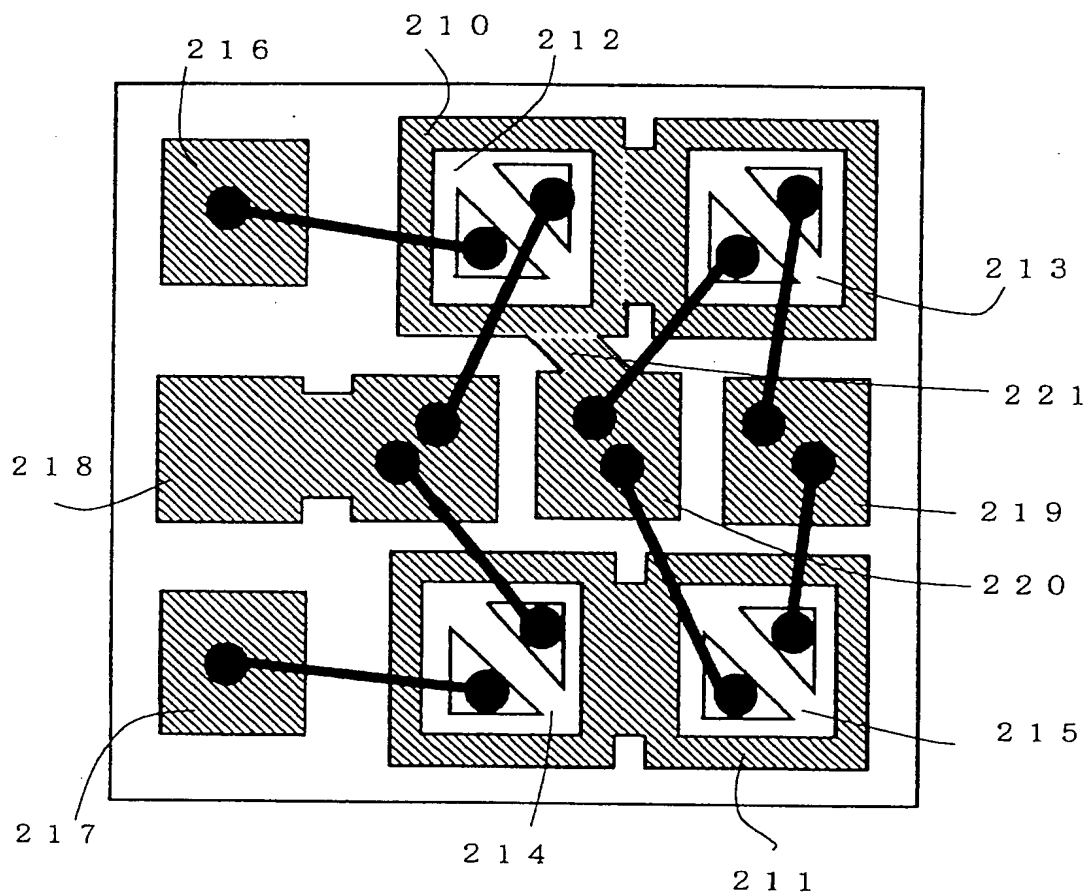


Fig.13

000001-2182560

Fig.14



000001-0102-0000

Fig.15

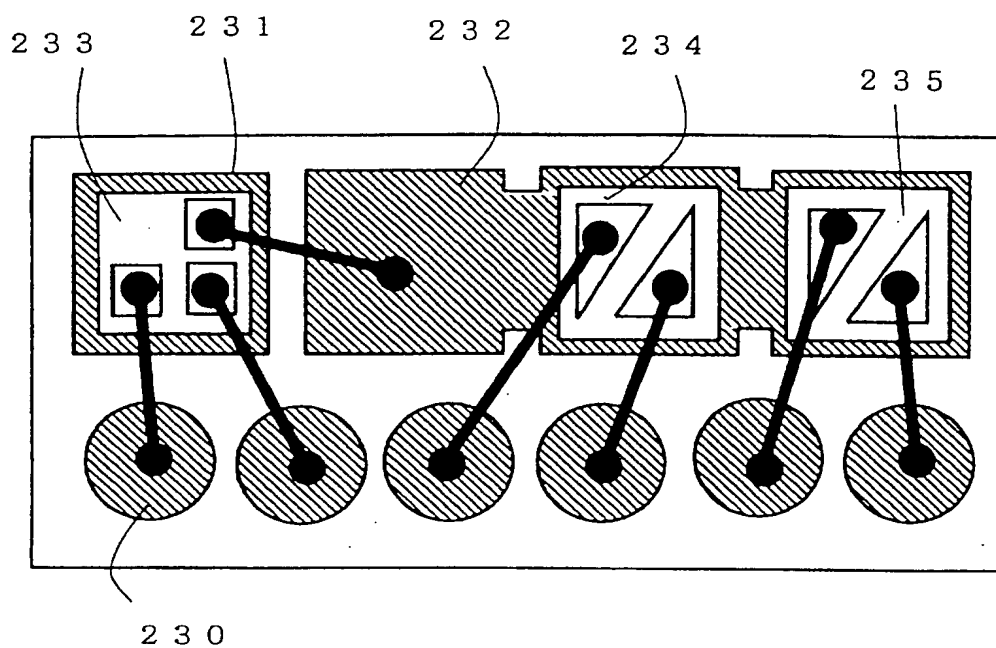
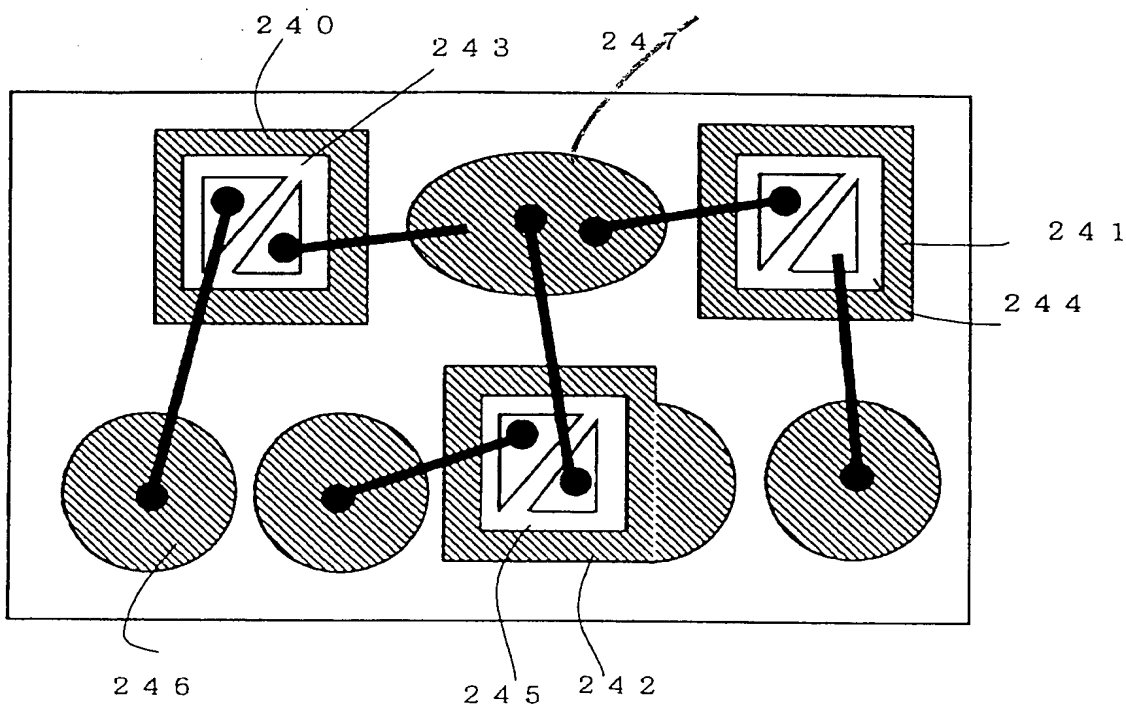
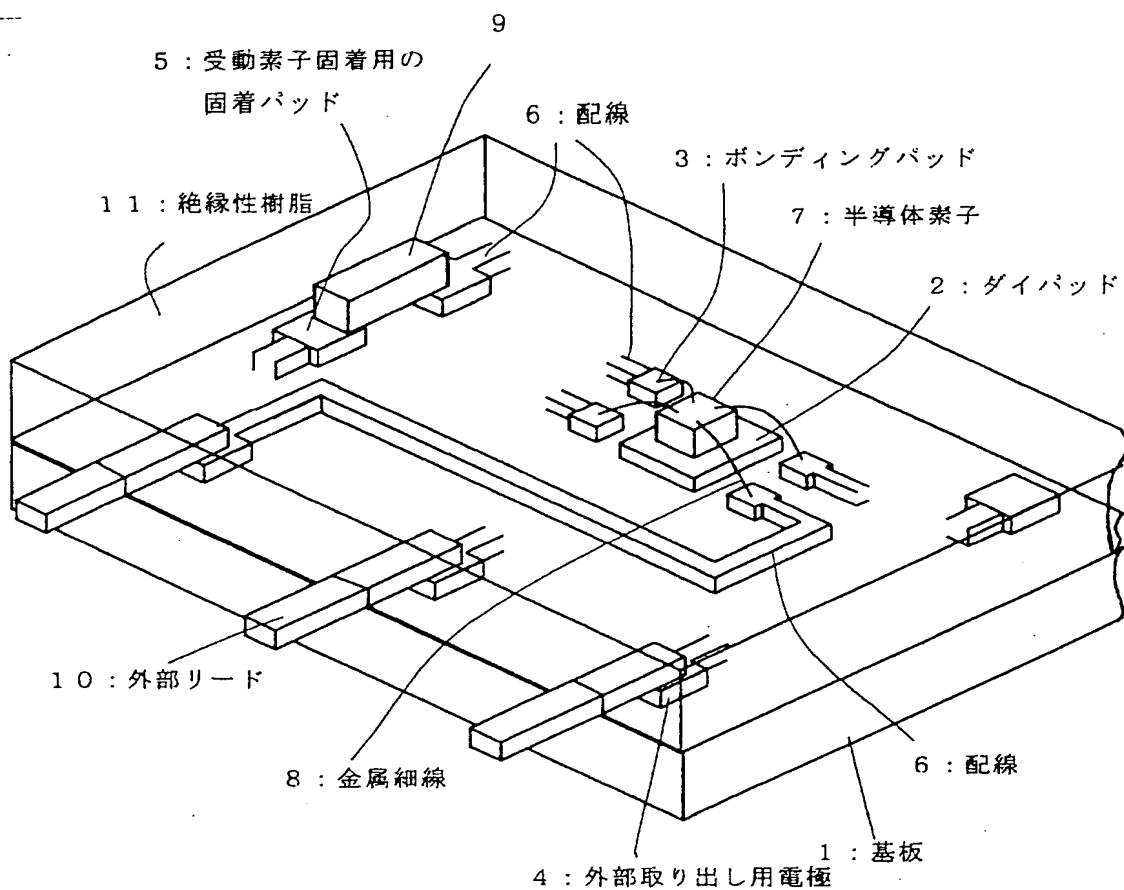


Fig.16



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Fig.17



000001-24152900

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Fig.18A

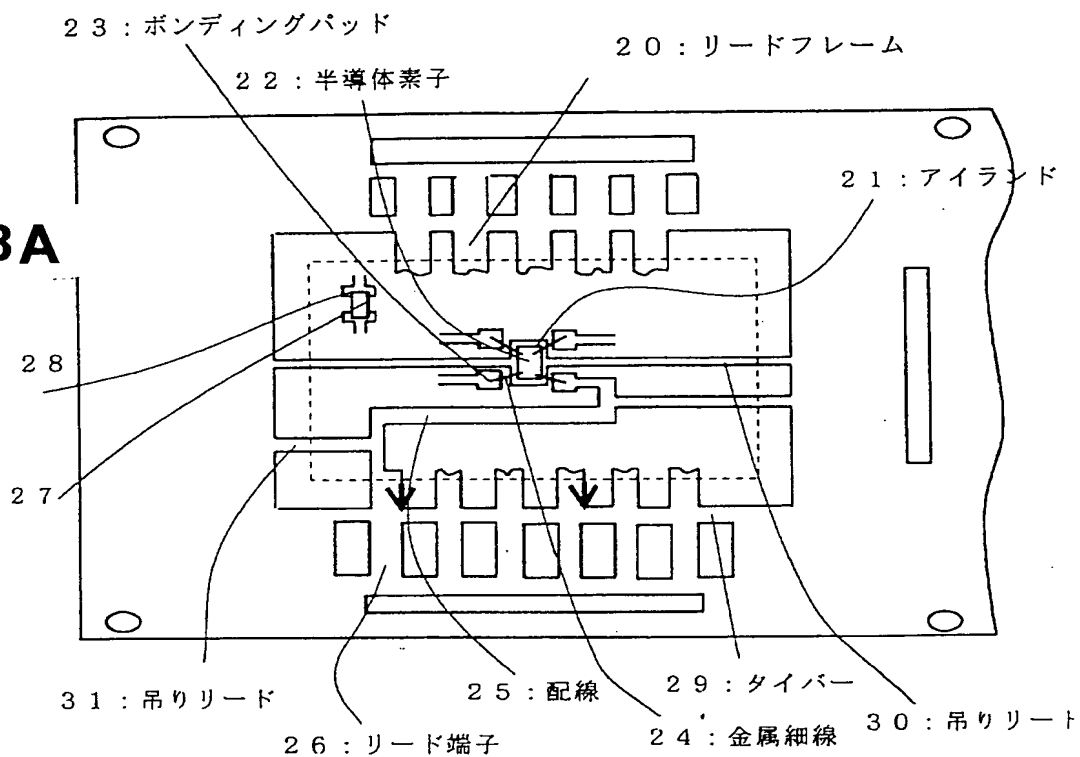


Fig.18B

